Pb Free Product



NCE P-Channel Enhancement Mode Power MOSFET

Description

The NCE4435 uses advanced trench technology to provide excellent R_{DS(ON)}, low gate charge and operation with gate voltages as low as 4.5V.

General Features

• $V_{DS} = -30V, I_{D} = -9.1A$

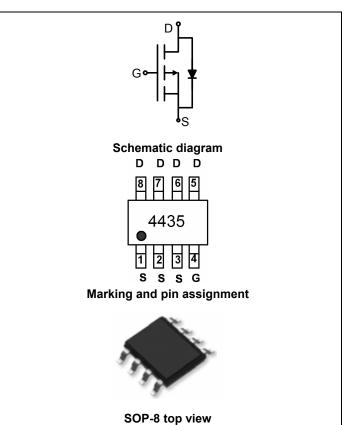
 $R_{DS(ON)}$ < 35m Ω @ V_{GS} =-4.5V

 $R_{DS(ON)}$ < 20m Ω @ V_{GS} =-10V

- High power and current handing capability
- Lead free product is acquired
- Surface mount package

Application

- Battery Switch
- Load switch
- Power management



Package Marking and Ordering Information

Device Marking	Device	Device Package	age Reel Size Tape width		Quantity
4435	NCE4435	SOP-8	Ø330mm	12mm	2500 units

Absolute Maximum Ratings (T_A=25℃unless otherwise noted)

Parameter		Symbol	Limit	Unit	
Drain-Source Voltage		V _{DS}	-30	V	
Gate-Source Voltage		V _G S	±20	V	
	T _C =25°C		-11		
Continuous Desir Courset (T450°C)	T _C =70°C	I _D	-9		
Continuous Drain Current (T _J =150°C)	T _A =25°C		-9.1	A	
	T _A =70°C		-7.2		
Drain Current-Pulsed (Note 1)		I _{DM}	-50	А	
Maximum Power Dissipation		P _D	3.1	W	
Operating Junction and Storage Temperatu	re Range	T_{J}, T_{STG}	-55 To 150	$^{\circ}\!\mathbb{C}$	

Thermal Characteristic

Thermal Resistance, Junction-to-Ambient (Note 2)	$R_{\theta JA}$	40	°C/W
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Electrical Characteristics (T_A=25 ℃ unless otherwise noted)



NCE4435

Parameter	Symbol	Condition	Min	Тур	Max	Unit
Off Characteristics			•	•		•
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} =0V I _D =-250μA	-30	-33	-	V
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =-30V,V _{GS} =0V	-	-	-1	μA
Gate-Body Leakage Current	I _{GSS}	V_{GS} =±20 V , V_{DS} =0 V	-	-	±100	nA
On Characteristics (Note 3)	<u>. </u>		•	•		•
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}$, $I_{D}=-250\mu A$	-1	-1.5	-3	V
Data Caraca Caraca Data Data Caraca	-	V _{GS} =-10V, I _D =-9.1A	-	16	20	mΩ
Drain-Source On-State Resistance	R _{DS(ON)}	V _{GS} =-4.5V, I _D =-6.9A	-	21	35	mΩ
Forward Transconductance	9 FS	V _{DS} =-15V,I _D =-9.1A	10	-	-	S
Dynamic Characteristics (Note4)			•	·		I.
Input Capacitance	C _{lss}	\/ 45\/\/ 0\/	-	1600	-	PF
Output Capacitance	C _{oss}	V_{DS} =-15V, V_{GS} =0V, F=1.0MHz	-	350	-	PF
Reverse Transfer Capacitance	C _{rss}	r=1.0Wnz	-	300	-	PF
Switching Characteristics (Note 4)	<u>. </u>		•	•		•
Turn-on Delay Time	t _{d(on)}		-	10	-	nS
Turn-on Rise Time	t _r	V _{DD} =-15V, ID=-1A,	-	15	-	nS
Turn-Off Delay Time	t _{d(off)}	V_{GS} =-10 V , R_{GEN} =6 Ω	-	110	-	nS
Turn-Off Fall Time	t _f			70	-	nS
Total Gate Charge	Qg	\/ - 45\/ - 0.40	-	30	-	nC
Gate-Source Charge	Q _{gs}	V _{DS} =-15V,I _D =-9.1A	-	5.5	-	nC
Gate-Drain Charge	Q_{gd}	V _{GS} =-10V	-	8	-	nC
Drain-Source Diode Characteristics				•		•
Diode Forward Voltage (Note 3)	V _{SD}	V _{GS} =0V,I _S =-2.1A	-	-	-1.2	V
				•		

Notes:

- 1. Repetitive Rating: Pulse width limited by maximum junction temperature.
- **2.** Surface Mounted on FR4 Board, $t \le 10$ sec.
- **3.** Pulse Test: Pulse Width ≤ 300μ s, Duty Cycle ≤ 2%.
- 4. Guaranteed by design, not subject to production



Typical Electrical and Thermal Characteristics

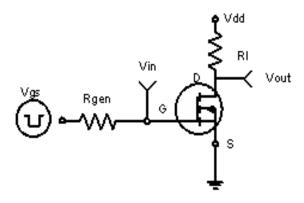


Figure 1:Switching Test Circuit

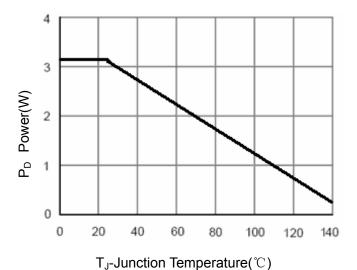


Figure 3 Power Dissipation

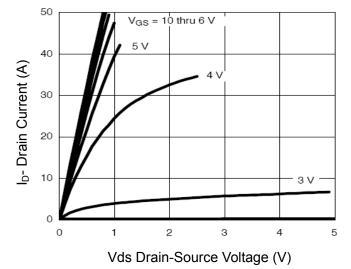


Figure 5 Output Characteristics

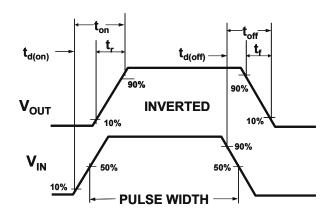


Figure 2:Switching Waveforms

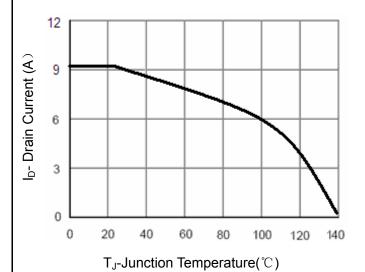


Figure 4 Drain Current

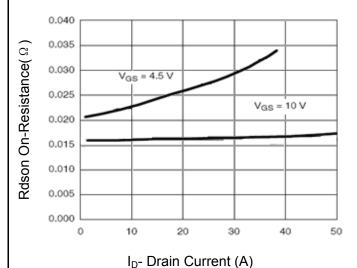


Figure 6 Drain-Source On-Resistance



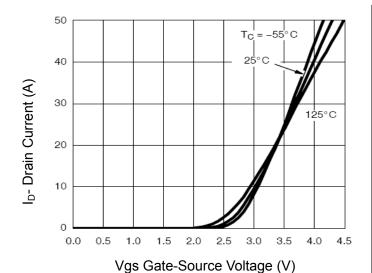
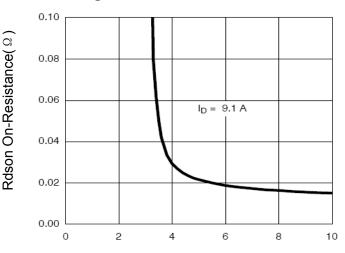


Figure 7 Transfer Characteristics



Vgs Gate-Source Voltage (V)

Figure 9 Rdson vs Vgs

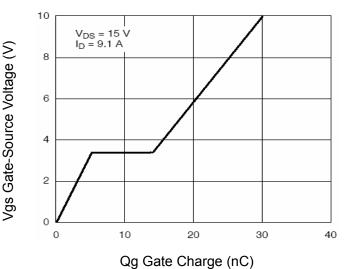


Figure 11 Gate Charge

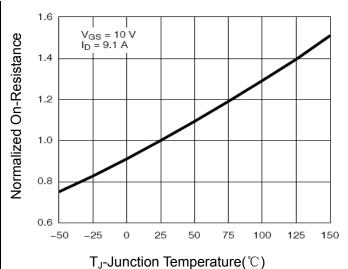
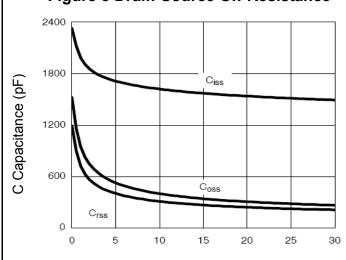


Figure 8 Drain-Source On-Resistance



Vds Drain-Source Voltage (V)

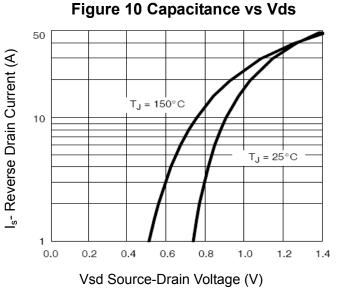
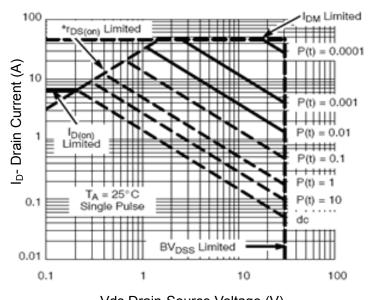


Figure 12 Source- Drain Diode Forward





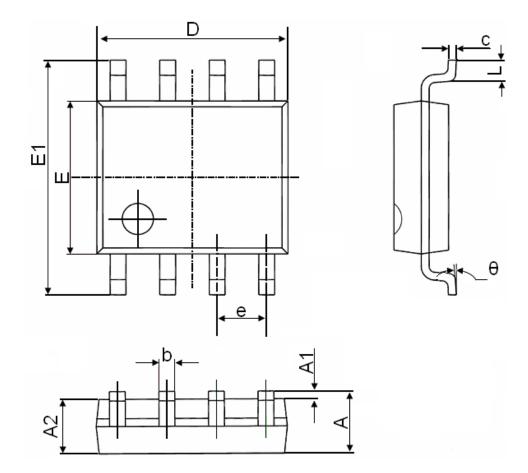
Vds Drain-Source Voltage (V)

Figure 13 Safe Operation Area Transient Thermal Impedance r(t), Normalized Effective Duty Cycle = 0.5 0.2 0.1 0.05 1. Duty Cycle, D = $\frac{t_1}{t_2}$ 2. Per Unit Base = R_{thJA} 0.02 3. $T_{JM} - T_A = P_{DM}Z_{thJA}(t)$ 4. Surface Mounted 0.01 10-2 10-4 10⁻³ 10⁻¹ 10 100 600 Square Wave Pluse Duration(sec)

Figure 14 Normalized Maximum Transient Thermal Impedance



SOP-8 Package Information



Symbol	Dimensions	In Millimeters	Dimensions In Inches		
Symbol	Min. Max. Min	Min.	Max.		
Α	1.350	1.750	0.053	0.069	
A1	0.100	0.250	0.004	0.010	
A2	1.350	1.550	0.053	0.061	
b	0.330	0.510	0.013	0.020	
С	0.170	0.250	0.006	0.010	
D	4.700	5.100	0.185	0.200	
Е	3.800	4.000	0.150	0.157	
E1	5.800	6.200	0.228	0.244	
е	1.270	(BSC)	0.050	(BSC)	
L	0.400	1.270	0.016	0.050	
θ	0°	8°	0°	8°	



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